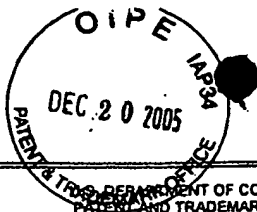


Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 246155US2SRD		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Masato KOYAMA, et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>SP</i>	AW	M. R. VISOKAY, et al., "APPLICATION OF HfSiON AS A GATE DIELECTRIC MATERIAL", Applied Physics Letters, Volume 80, Number 17, April 29, 2002, Pages 3183-3185					
<i>SP</i>	AX	R. A. McKEE, et al., "PHYSICAL STRUCTURE AND INVERSION CHARGE AT A SEMICONDUCTOR INTERFACE WITH A CRYSTALLINE OXIDE", Science Magazine, Vol. 293, July 20, 2001, Pages 468-471					
	AY						
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner <i>SP</i>					Date Considered <i>2/27/06</i>		
<small>*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							



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	AZ	

☐ Additional References sheet(s) attached

Examiner

S. J. Lee

Date Considered

2/27/06

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*: Same as the 12/04/2003 IDS